

**WHAT IS CLAIMED IS:**

1. A protection circuit for a radio frequency (RF) power amplifier, the RF power amplifier operable to receive an RF input signal and amplify the RF input signal, the protection circuit comprising:

shunt circuitry operable to shunt an RF input signal to AC ground, the shunt circuitry including,

a shunt switch operable to shunt the RF input signal to AC ground and release the RF input signal from AC ground, the shunt switch being controlled by control circuitry; and

the control circuitry including ramp circuitry, the ramp circuitry operable to control the shunt switch so that the shunt switch gradually releases the RF signal from AC ground for input to an RF amplifier.

2. The protection circuit of claim 1, wherein the shunt switch comprises a linear region MOSFET.

3. The protection circuit of claim 2, wherein the linear region MOSFET is an NMOS transistor.

4. The protection circuit of claim 1, wherein the ramp circuitry includes an RC network.

5. The protection circuit of claim 4, wherein the shunt switch gradually releases the RF signal from AC ground exponentially.

6. The protection circuit of claim 4, wherein the ramp circuitry releases in accordance with a discharge of a capacitor in the RC network.

7. The protection circuit of claim 1, further comprising bias shutdown circuitry operable to shut off a bias voltage or a bias current being supplied to an output transistor of the RF power amplifier.

8. The protection circuit of claim 7, further comprising peak detection circuitry operable to monitor an output voltage of the RF amplifier and provide a protection signal to the shunt circuitry and the bias shutdown circuitry when the output voltage of the RF amplifier exceeds a threshold voltage level.

9. The protection circuit of claim 8, wherein the threshold voltage level is programmable through the peak detection circuitry.

10. The protection circuit of claim 1, wherein the control circuitry further includes delay circuitry operable to delay the ramp control circuitry from gradually releasing the RF input signal from AC ground.

11. The protection circuit of claim 10, wherein the delay circuitry includes an RC network.

12. A protection circuit for a radio frequency (RF) power amplifier, the RF power amplifier operable to receive an RF input signal and amplify the RF input signal, the protection circuit comprising:

shunting means for shunting the RF input signal to AC ground and releasing the RF input signal from AC ground, the shunting means being controlled by control means; and

the control means for controlling the shunting means so that the shunting means gradually releases the RF signal from AC ground for input to an RF amplifier.

13. The protection circuit of claim 12, wherein the shunting means comprises a linear region MOSFET.

14. The protection circuit of claim 13, wherein the linear region MOSFET is an NMOS transistor.

15. The protection circuit of claim 12, wherein the control means includes an RC network.

16. The protection circuit of claim 15, wherein the shunting means gradually releases the RF signal from AC ground exponentially.

17. The protection circuit of claim 15, wherein the control means controls the shunting means to release the RF signal from AC ground in accordance with a discharge of a capacitor in the RC network.

18. The protection circuit of claim 12, further comprising biasing means for shutting off a bias voltage or a bias current being supplied to an output transistor of the RF power amplifier.

19. The protection circuit of claim 18, further comprising detecting means for monitoring an output voltage of the RF amplifier and providing a protection signal to the shunting means and the biasing means when the output voltage of the RF amplifier exceeds a threshold voltage level.

20. The protection circuit of claim 19, wherein the threshold voltage level is programmable through the detecting means.

21. The protection circuit of claim 12, wherein the control means further includes delay means for delaying the shunting means from gradually releasing the RF input signal from AC ground.

22. The protection circuit of claim 21, wherein the delay means includes an RC network.

23. An RF power amplifier, comprising:  
amplifier circuitry operable to amplify an RF input signal and provide an amplified RF output signal;  
peak detection circuitry operable to monitor the amplified output RF signal and detect when the amplified output signal exceeds a threshold voltage level; and

a bias network operable to provide a bias to the amplifier circuitry and shut off the bias to the amplifier circuitry when the peak detection circuitry detects that the amplified output signal has exceeded the threshold voltage level.

24. The RF power amplifier of claim 23, wherein the bias network is operable to further turn off an output transistor of the amplifier circuitry when the peak detection circuitry detects that the amplified output signal has exceeded the threshold voltage level.

25. The RF power amplifier of claim 23, further comprising shunt circuitry operable to shunt the RF input signal to AC ground when the peak detection circuitry detects that the amplified output signal has exceeded the threshold voltage level.

26. The RF power amplifier of claim 25, wherein the shunt circuitry comprises:

a shunt switch operable to shunt the RF input signal to AC ground and release the RF input signal from AC ground, the shunt switch being controlled by control circuitry; and

the control circuitry including ramp circuitry, the ramp

circuitry operable to control the shunt switch so that the shunt switch gradually releases the RF signal from AC ground for input to an RF amplifier.

27. The RF power amplifier of claim 26, wherein the shunt switch comprises a linear region MOSFET.

28. The RF power amplifier of claim 27, wherein the linear region MOSFET is an NMOS transistor.

29. The RF power amplifier of claim 26, wherein the ramp circuitry includes an RC network.

30. The RF power amplifier of claim 26, wherein the control circuitry further includes delay circuitry operable to delay the ramp control circuitry from gradually releasing the RF input signal from AC ground.

31. A method for protecting an RF power amplifier from elevated output voltages, the method comprising:

detecting an output voltage of an RF power amplifier exceeding a threshold voltage level;

shutting off bias to an output transistor of the RF power amplifier when the output voltage exceeds the threshold

voltage level; and

turning off the output transistor of the RF power amplifier when the output voltage exceeds the threshold voltage level.

32. The method of claim 31, further comprising:

shunting an RF input signal to the RF power amplifier to AC ground when the output voltage exceeds the threshold voltage level.

33. The method of claim 32, further comprising:

supplying bias to the output transistor and turning on the output transistor when the output voltage is reduced to a level below the threshold voltage level.

34. The method of claim 33, further comprising:

gradually releasing the RF input signal from AC ground when the output voltage is reduced to a level below the threshold voltage level.

35. The method of claim 34, further comprising:

delaying the gradual release of the RF input signal from AC ground until a time after the output transistor has turned



on.

36. The method of claim 32, further comprising providing an asymmetrical control that quickly shuts off the power amplifier and gradually turns on the power amplifier at a gradual rate.

37. A protection circuit for an RF power amplifier, the protection circuit comprising:

means for detecting an output voltage of an RF power amplifier exceeding a threshold voltage level;

means for shutting off bias to an output transistor of the RF power amplifier when the output voltage exceeds the threshold voltage level; and

means for turning off the output transistor of the RF power amplifier when the output voltage exceeds the threshold voltage level.

38. The protection circuit of claim 37, further comprising:

means for shunting an RF input signal to the RF power amplifier to AC ground when the output voltage exceeds the threshold voltage level.

39. The protection circuit of claim 38, further comprising:

means for supplying bias to the output transistor and  
means for turning on the output transistor.

40. The protection circuit of claim 39, further comprising:

means for gradually releasing the RF input signal from AC ground when the output voltage is reduced to a level below the threshold voltage level.

41. The protection circuit of claim 40, further comprising:

means for delaying the gradual release of the RF input signal from AC ground until a time after the output transistor has turned on.

42. A wireless transceiver, comprising:

an RF power amplifier operable to amplify an RF input signal, the RF power amplifier including,

amplifier circuitry operable to amplify the RF input signal and provide an amplified RF output signal;

peak detection circuitry operable to monitor the amplified output RF signal and detect when the amplified

output signal exceeds a threshold voltage level; and

a bias network operable to provide a bias to the amplifier circuitry and shut off the bias to the amplifier circuitry when the peak detection circuitry detects that the amplified output signal has exceeded the threshold voltage level.

43. The wireless transceiver of claim 42, wherein the bias network is operable to further turn off an output transistor of the amplifier circuitry when the peak detection circuitry detects that the amplified output signal has exceeded the threshold voltage level.

44. The wireless transceiver of claim 42, wherein the RF amplifier further comprises shunt circuitry operable to shunt the RF input signal to AC ground when the peak detection circuitry detects that the amplified output signal has exceeded the threshold voltage level.

45. The wireless transceiver of claim 44, wherein the shunt circuitry comprises:

a shunt switch operable to shunt the RF input signal to AC ground and release the RF input signal from AC ground, the shunt switch being controlled by control circuitry; and

the control circuitry including ramp circuitry, the ramp circuitry operable to control the shunt switch so that the shunt switch gradually releases the RF signal from AC ground for input to an RF amplifier.

46. The wireless transceiver of claim 45, wherein the shunt switch comprises a linear region MOSFET.

47. The wireless transceiver of claim 46, wherein the linear region MOSFET is an NMOS transistor.

48. The wireless transceiver of claim 45, wherein the ramp circuitry includes an RC network.

49. The wireless transceiver of claim 45, wherein the control circuitry further includes delay circuitry operable to delay the ramp control circuitry from gradually releasing the RF input signal from AC ground.

50. The wireless transceiver of claim 42, wherein the wireless transceiver is compliant with an IEEE standard selected from the group consisting of 802.11, 802.11a, 802.11b, 802.11e, 802.11g, 802.11h, and 802.11i, and 802.14.

51. An RF power amplifier, comprising:

amplifying means for amplifying an RF input signal and providing an amplified RF output signal;

detecting means for monitoring the amplified output RF signal and detecting when the amplified output signal exceeds a threshold voltage level; and

biasing means for providing a bias to the amplifying means and shutting off the bias to the amplifying means when the detecting means detects that the amplified output signal has exceeded the threshold voltage level.

52. The RF power amplifier of claim 51, wherein the biasing means is operable to further turn off an output transistor of the amplifying means when the detecting means detects that the amplified output signal has exceeded the threshold voltage level.

53. The RF power amplifier of claim 51, further comprising shunting means for shunting the RF input signal to AC ground when the detecting means detects that the amplified output signal has exceeded the threshold voltage level.

54. The RF power amplifier of claim 53, wherein the shunting means comprises:

switching means for shunting the RF input signal to AC ground and releasing the RF input signal from AC ground, the switching means being controlled by control circuitry; and

the control circuitry including ramping means for controlling the switching means so that the switching means gradually releases the RF signal from AC ground for input to an RF amplifier.

55. The RF power amplifier of claim 54, wherein the switching means comprises a linear region MOSFET.

56. The RF power amplifier of claim 55, wherein the linear region MOSFET is an NMOS transistor.

57. The RF power amplifier of claim 54, wherein the ramping means includes an RC network.

58. The RF power amplifier of claim 54, wherein the control circuitry further includes delaying means for delaying the ramping means from gradually releasing the RF input signal from AC ground.

59. A wireless transceiver, comprising:

an RF power amplifier operable to amplify an RF input

signal, the RF power amplifier including,

amplifying means for amplifying the RF input  
signal and provide an amplified RF output signal;

detecting means for monitoring the amplified output  
RF signal and detecting when the amplified output signal  
exceeds a threshold voltage level; and

biasing means for providing a bias to the  
amplifying means and shutting off the bias to the  
amplifying means when the detecting means detects that  
the amplified output signal has exceeded the  
threshold voltage level.

60. The wireless transceiver of claim 59, wherein the  
biasing means is operable to further turn off an output  
transistor of the amplifying means when the detecting means  
detects that the amplified output signal has exceeded the  
threshold voltage level.

61. The wireless transceiver of claim 59, wherein the RF  
amplifier further comprises shunting means for shunting the RF  
input signal to AC ground when the detecting means detects  
that the amplified output signal has exceeded the threshold  
voltage level.

62. The wireless transceiver of claim 61, wherein the shunting means comprises:

switching means for shunting the RF input signal to AC ground and releasing the RF input signal from AC ground, the switching means being controlled by control circuitry; and

the control circuitry including ramping means for controlling the switching means so that the switching means gradually releases the RF signal from AC ground for input to an RF amplifier.

63. The wireless transceiver of claim 62, wherein the switching means comprises a linear region MOSFET.

64. The wireless transceiver of claim 63, wherein the linear region MOSFET is an NMOS transistor.

65. The wireless transceiver of claim 62, wherein the ramping means includes an RC network.

66. The wireless transceiver of claim 62, wherein the control circuitry further includes delaying means for delaying the ramping means from gradually releasing the RF input signal from AC ground.



67. The wireless transceiver of claim 59, wherein the wireless transceiver is compliant with an IEEE standard selected from the group consisting of 802.11, 802.11a, 802.11b, 802.11e, 802.11g, 802.11h, and 802.11i, and 802.14.